DATA SHEET



MB8421/8422-90/-90L/-90LL/-12/-12L/-12LL CMOS 16K-BIT DUAL-PORT SRAM

2K x 8 Bits CMOS Dual-Port Static Random Access Memory

The Fujitsu MB8421 and MB8422 are 2,048 words x 8 bits dual-port high-performance static random access memories (SRAMs) fabricated in CMOS. The SRAMs use asynchronous circuits; thus, no external clocks are required. MB8421 and MB8422 provide the user with two separately controlled I/O ports with independent addresses, Chip Select (CS), Write Enable (WE), Output Enable (OE), and I/O functions. This arrangement permits independent access to any memory location for either a Read or Write operation — a useful feature for shared data processing applications. These devices have an automatic power-down feature controlled by CS.

To avoid data contention on the same address, a BUSY input is provided for address arbitration; in addition, MB8421 utilizes an interrupt (INT) flag which allows communication between systems on either side of the RAM. Both devices use a single +5 V power supply and all pins are TTL-compatible.

Some typical applications for these memory devices are multiprocessing systems, distributed networks, external register files, and peripheral controllers.

Organization: 2,048 words x 8 bits

Static operation: no clocks or timing strobe required

Access time: $t_{AA} = t_{ACS} = 90 \text{ ns max.}$ (MB8421/22-90)

(MB8421/22-90L) (MB8421/22/-90LL)

 $t_{AA} = t_{ACS} = 120 \text{ ns max.}$ (MB8421/22-12)

(MB8421/22-12L) (MB8421/22/-12LL)

Power consumption for the standard version:

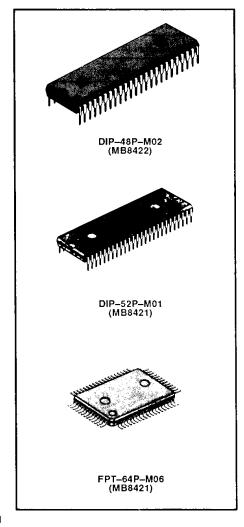
660 mW max. (Both ports active)
385 mW max. (One port active)
38.5 mW max. (Both ports standby, TTL)
11 mW max. (Both ports standby, CMOS)

Power consumption for the L and LL-versions:

495 mW max. (Both ports active)
275 mW max. (One port active)
27.5 mW max. (Both ports standby, TTL)
1.1 mW max. (Both ports standby, CMOS)

- Single +5 V power supply ±10% tolerance
- TTL compatible inputs and outputs
- Three-state outputs with OR-tie capacity
- Electrostatic protection for all inputs and outputs
- Address arbitration function: BUSY flag
- Interrupt function for communication between systems (MB8421 only): INT flag
- Data retention voltage: 2 V min.
- Standard Plastic Packages:

48-pin DIP MB8422-xx(L/LL)P 52-pin DIP MB8421-xx(L/LL)P 64-pin QFP MB8421-xx(L/LL)PFQ



This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

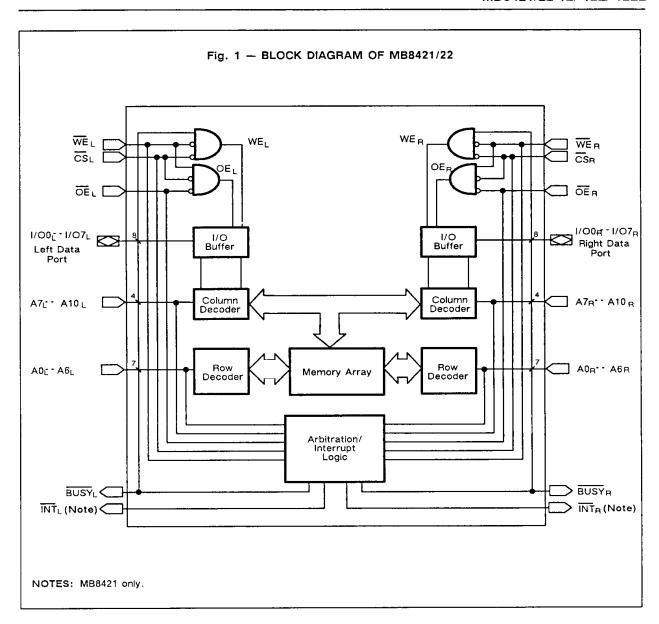
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Parameter	Designator	Value	Unit
Supply Voltage	V _{cc}	-0.5 to +7	V
Input Voltage on any pin with respect to V _{SS}	VIN	-0.5 to V _{CC} +0.5	V
Output Voltage on any I/O pin with respect to V _{SS}	VOUT	-0.5 to V _{CC} +0.5	V
Output Current	IOUT	<u>+</u> 20	mA
Power dissipation	PD	1.0	w
Temperature Under Blas	TBIAS	-10 to +85	_
Storage Temperature	TSTG	-40 to +125	°c

NOTE:

Permanent device damage may occur if the above **Absolute Maximum Ratings** are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

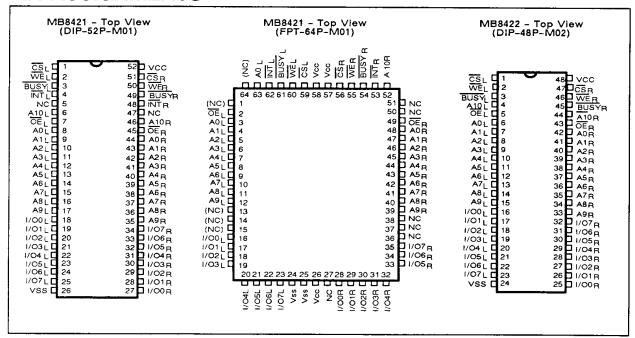
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I/O CAPACITANCE (T_A = 25 °C, f = 1 MHz)

Parameter	Symbol	Тур	Max	Unit
Input Capacitance (VIN = 0V)	CIN		10	pF
I/O Capacitance (VI/O = 0V)	CI/O		10	pF

PIN ASSIGNMENTS



PIN DESCRIPTIONS

Left Port	Right Port	Function	Left Port	Right Port	Function
WEL	WER	Write Enable	ĪNT _L	ĪNT _B	Interrupt Flag
<u>C</u> SL	CSR	Chip Select	7/ 	+ · · · · · · · · · · · · · · · · · · ·	<u> </u>
ŌĒL	ŌĒ R	Output Enable	A0L A10L	A0R A10R	Address
BUSYL	BUSYR	Busy Flag		I/O0R I/O7R	Data Input/Output
		Vcc			Power (Common)
		Vss			Ground (Common)

FUNCTIONAL OPERATION

The MB8421 and MB8422 provide two ports with separate control signals, address inputs, and input/output data pins that allow asynchronous read and write operations to any memory location. Each device has an on-chip automatic power-down feature controlled by $\overline{\text{CS}}$ that places the respective port in the standby mode when the chip is deselected $\overline{\text{CS}}$ is HIGH).

When a port is enabled, access to the entire memory array is permitted. Each port has an independent Output Enable (OE) control that is active in the read mode and enables the output drivers. Non-contention Read/Write conditions are shown in the following Truth Table; a simplified block diagram of the dual-port SRAM is shown in Fig. 1.

NON-CONTENTION READ/WRITE CONTROL

LEFT PO	ORT IN	PUTS ¹	RIGHT	PORT IN	IPUTS ¹	FLA	AGS	FUNCTION
R/WL		OEL	R/WR	CSR	OER	BUSYL	BUSYR	FONCTION
×	Н	X	Х	×	X	Н	Н	Left Port in Power Down Mode
X	×	×	Х	Н	Х	н н		Right Port in Power Down Mode
L	L	Х	Х	X	Х	Н	Н	Data on Left Port Written Into Memory
Н	L	L	Х	Х	X	н	H	Data in Memory Output on Left Port
X	×	Х	L	Ļ	Х	Н.,	H	Data on Right Port Written Into Memory
X	×	Х	Н	L	L	Н	н	Data in Memory Output on Right Port

NOTES:

- 1. $A0_L-A10_L \neq A0_R A10_R$
- 2. H = HIGH, L = LOW, X = Don't Care

ARBITRATION LOGIC

The arbitration logic resolves an address match or chip-enable match and determines the access priority. In both cases, an active BUSY flag is set for the port-in-waiting. Since both ports are asynchronous, there is the possibility of accessing the same memory location from both sides. In the read mode, this condition is not a problem. However, this is a problem when both ports are in a write mode with different data words or when one port is reading and the other is writing. When both ports access the same memory location, the on-chip arbitration logic determines which port has access and the BUSY flag for the delayed port is set active LOW and all operations on that port are inhibited. The delayed port can be accessed when the BUSY flag becomes inactive. Basic modes of abitration are described in subsequent paragraphs.

- When addresses for both the left and right ports match and are valid before S Is active, the on-chip control logic arbitrates between S L and S F for device access. Refer to the following Truth Table for signal states; timing detail is shown later in this data sheet under "Data Contention Cycle No. 2 (S controlled)."
- When \(\overline{\overline{CS}_L}\) and \(\overline{\overline{CS}_R}\) are LOW before an address match, on-chip control logic arbitrates between the left and right addresses for device access. Signal states for this condition are shown in the following Truth Table; timing detail is shown under "Data Contention Cycle No. 1 (Address Controlled)."

ARBITRATION WITH ADDRESS MATCH BEFORE CS

	L	EFT PO	DRT		R	IGHT F	PORT	FLA	AGS	FUNCTION
R/WL	CSL	OEL	A0 L-A10 L	R/WR	CSR	OEA	A0 _R -A10 _R	BUSYL	BUSYR	Fonction
х	LBR	×	MATCH	х	L	×	MATCH	Н	L	Left Operation Permitted Right Operation Not Permitted
Х	L	×	МАТСН	×	LBL	Х	MATCH	L	н	Right Operation Permitted Left Operation Not Permitted
Х	LST	х	MATCH	Х	LST	х	матсн	н	L	Arbitration Resolved

NOTES: X = Don't Care, L = Low, H = High, LST= Low Same Time, LBR = Low Before Right, LBL = Low Before Left

ADDRESS ARBITRATION WITH CS LOW BEFORE ADDRESS MATCH

	L	EFT PC	ORT		R	IGHT F	ORT	FLA	\GS	FUNCTION
R/WL	CSL	OEL	A0A10_	R/W _R	CSR	OER	A0 R-A10 R	BUSYL	BUSYR	FUNCTION
×	L	Х	VBR	х	L.	×	VALID	Н	<u>ا</u>	Left Operation Permitted Right Operation Not Permitted
×	L	Х	VALID	×	L	Х	VBL	L	н	Right Operation Permitted Left Operation Not Permitted
Х	L	х	VST	Х	L	Х	VST	н	L	Arbitration Resolved

NOTES: X = Don't Care, L = Low, H = High, VST = Valid Same Time, VBR = Valid Before Right, VBL = Valid Before Left

When both $\overline{\text{CS}}_{\text{L}}$ and $\overline{\text{CS}}_{\text{R}}$ are low at the same time ($\overline{\text{CS}}$ controlled) or when both left-and-right addresses are valid at the same time (address controlled), the $\overline{\text{BUSY}}_{\text{R}}$ flag for the right port is set to the active LOW state and access is granted to the left port.

For the Intel 8086 and Fujitsu's MBL8086 as well as most other microprocessors, the asynchronous BUSY signal can be directly tied to the READY input, providing setup-and-hold time requirements are met.

INTERRUPT FUNCTION

The interrupt $\overline{(\text{INT})}$ function provides communication between systems on both sides of the dual-port RAM. $\overline{\text{INT}_L}$ is set LOW when the processor on the right port writes to address 7FE (A0 = L and A1-A10 = H). When the left port acknowledges by reading address 7FE, $\overline{\text{INT}_L}$ is then reset to HIGH. In essence, address 7FE serves as an 8-bit mailbox that transfers information from the right port to the left port. When $\overline{\text{INT}_R}$ is set LOW, the processor on the left port writes to address 7FF (A0-A10=H). When the right port

acknowledges by reading address 7FF. $\overline{\text{INT}}_{R}$ is then reset to HIGH. Hence, address 7FF serves as a second 8-bit mailbox, transferring information from the left port to the right port.

On power-up, $\overline{\text{INT}}_{\text{L}}$ and $\overline{\text{INT}}_{\text{R}}$ are set to a HIGH state. However, if one port is in the standby mode, the standby port can still be interrupted by the processor on the other port. But if the $\overline{\text{BUSY}}$ flag is set to the LOW state, the port associated with that flag cannot set or reset the $\overline{\text{INT}}$ flag.

RECOMMENDED OPERATING CONDITIONS

(Referenced to Vss)

Parameter	Symbol		Value				
		Min	Тур	Max	Unit		
Supply Voltage	Vcc	4.5	5.0	5.5	V		
Operating Temperature	TA	0		70	°c		

DC CHARACTERISTICS

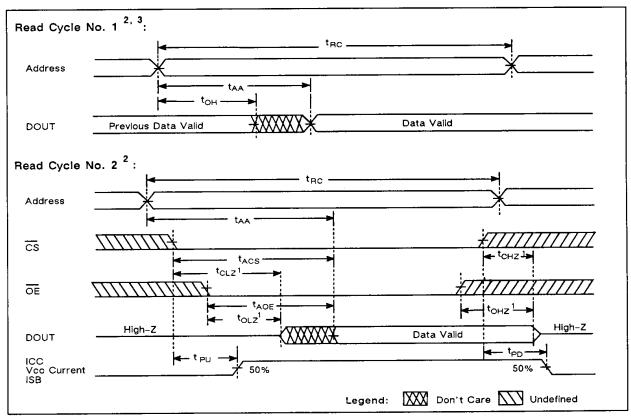
(Recommended Operating Conditions unless otherwise noted.)

Parameter	Symbol	Condition	MB842 MB8422		MB8421/ -90L/-90	MB8422 LL/-12L/-12LL	Unit
			Min	Max	Min	Max	
Operating Supply Current (Both ports Active)	ICC	Cycle = Min Duty = 100% IOUT = 0 mA		120		90	mA
	ISB1	Both ports at Standby		7		5	mA
<u>Standby</u>	ISB2	One port at Standby CS _L or CS _R =VIH, IOUT = 0 mA		70		50	mA
Supply Current	ISB3	Both ports at Full Standby CS _L & CS _R ≥ Vcc -0.2V		2		0.2	mA
	ISB4	One port at Full Standby CSL or CS _R > Vcc -0.2V IOUT = 0 mA		70		50	mA
Input Leakage Current	ILI	VIN = 0V to Vcc	-10	10	-10	10	μА
Output Leakage Current	ILO	CS = VIH, VOUT = 0V to Vcc	-10	10	-10	10	μΑ
Input High Voltage	VIH		2.2	Vcc +0.3	2.2	Vcc +0.3	V
Input Low Voltage	VIL		-0.3	0.8	-0.3	0.8	V
Output High Voltage	VOH (Note)	IOUT = -1.0 mA	2.4		2.4		V
Output Low Voltage	VOL	IOUT = 3.2 mA		0.4		0.4	
Output Low Voltage for Open-Drain	VOL	IOUT = 8 mA	-	0.4		0.4	V

NOTE: The BUSY and INT pins require pull-up resistors because they are open-drain outputs.

AC CHARACTERISTICS

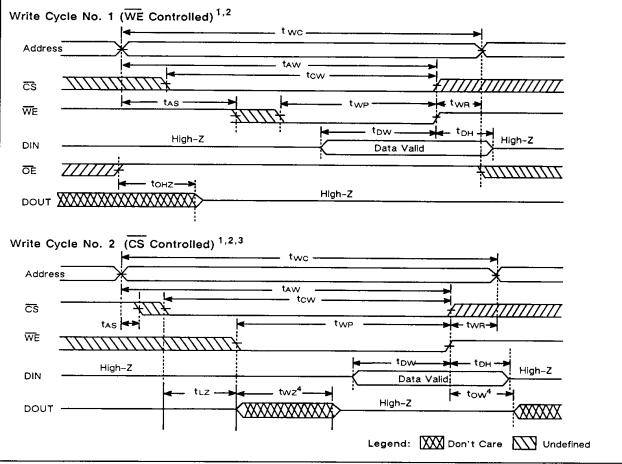
	Symbol		MB8421-90/90L/90LL MB8422-90/90L/90LL		12/12L/12LL 12/12L/12LL	Unit
Parameter	Symbol	Min	Max	Min	Max	
Read Cycle Parameters & Timing Diag	rams			.3		
Read Cycle Time	t _{RC}	90		120		ns
Address Access Time	t _{AA}		90		120	ns
Chip Select Access Time	t _{ACS}		90		120	ns
Output Enable Access Time	^t AOE		40		50	ns
Output Hold from Address Change	t _{OH}	10		10		ns
Chip Select to Output Low-Z (Note 1)	t _{CLZ}	5		5		ns
Output Enable to Output Low-Z (Note 1)	toLZ	5		5	ļļ.	ns
Chip Select to Output High-Z (Note 1)	t _{cHZ}		40		50	ns
Output Enable to Output High-Z (Note 1)	t _{ohz}		40		50	ns
Power up from Chip Select	t _{PU}	0		0		ns
Power down from Chip Select	t _{PD}		50		60	ns



NOTES:

- Transition is measured at a point of ± 500 mV from steady-state voltage with an output capacitance of 5pF.
 WE is High during read cycle.
 Device is continuously selected (CS = OE = VIL).

Parameter	Symbol		90/90L/90LL 90/90L/90LL	MB8421-1 MB8422-1	Unit	
	1	Min	Max	Min	Max	Onn
Write Cycle Parameters & Timing Diag	rams			1.	War. :	
Write Cycle Time	twc	90		120	Π	ns
Address Valid to End of Write	taw	85		100		ns
Chip Select to End of Write	tcw	85		100		ns
Address Setup Time	t _{AS}	0		0	† † -	ns
Write Pulse Width	t _{WP}	60		70		ns
Write Recovery Time	t _{WR}	0		0		ns
Data Valid to End of Write	t _{DW}	40		40	 	ns
Data Hold Time	t _{DH}	0		0	† †	ns
Write Enable to Output Low-Z (Note 4)	tow	0		0		ns
Write Enable to Output High-Z (Note 4)	t _{WZ}	1	40	-	50	ns

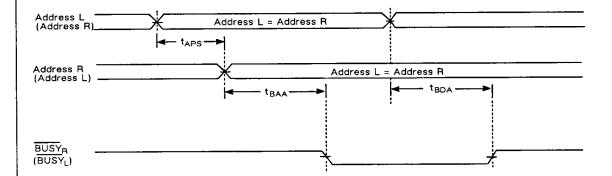


NOTES:

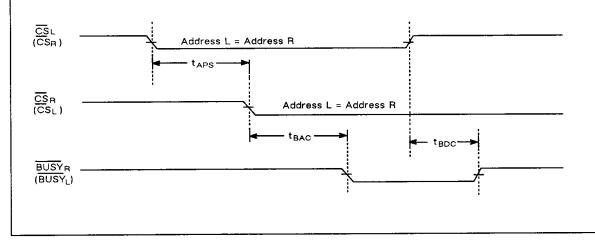
- 1. The Write Enable (WE) signal must be high during an address transition.
- 2. If the Output Enable (OE) and Chip Select (CS) signals are in the Read Mode, the associated I/O pins are in the output state; accordingly, input signals of opposite phase must not be applied to the outputs.
- 3. If CS goes high prior to or coincident with the low-to-high transition of WE, the output remains in high-impedance state.
- 4. This parameter is specified at a point ± 500 mV from steady-state voltage with an output capacitance of 5 pF.

Parameter	Symbol		1-90/90L 2-90/90L	MB8421 MB8422	Unit	
Farameter		Min	Max	Min	Max	
BUSY Parameters & Data Contention	Timing				Art Lighter	
BUSY Access Time from Address	t _{BAA}	I	45		60	ns
BUSY Output High-Z from Address	t _{BDA}		45	1	60	ns
BUSY Access Time from CS	t _{BAC}		45		60	ns
BUSY Output High-Z from CS	t _{BDC}		45]	60	ns
Arbitration Priority Set up Time	t _{APS}	20		25		ns

Data Contention Cycle No. 1 (Address Controlled)^{1, 2}:

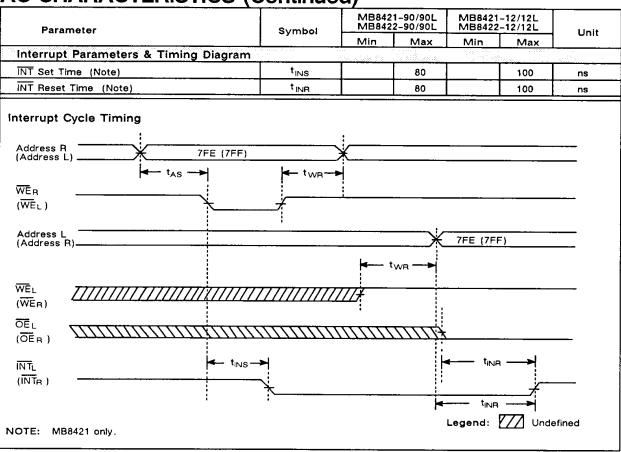


Data Contention Cycle No. 2 (CS Controlled)^{1, 3}:



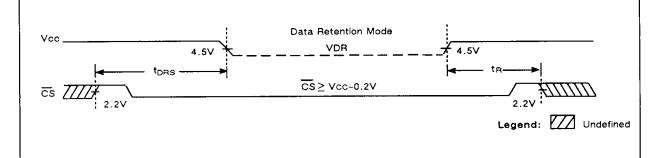
NOTES:

- 1. In case of dual-access at the same memory location, the port that accesses the RAM first sets the BUSY flag HIGH.
- 2. Chip Select (CS) signal must be low before or coincident with an address transition.
- 3. Address is valid prior to or coincidence with the high-to-low transition of $\overline{\text{CS}}$.



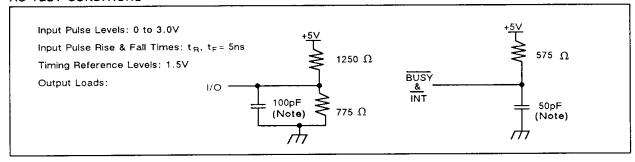
DATA RETENTION PARAMETERS & TIMING

Parameter	Symbol		1-90/12 2-90/12	MB8421 MB8422	Unit	
Parameter	- Cymbol	Min	Max	Min	Max	
Data Retention Parameters & Timing						
Data Retention Supply Voltage	VDR	2.0	5.5	2.0	5.5	V
Data Retention Supply Current (Note)	IDR		0.2		0.02	mA
Data Retention Setup Time	t DRS	0		0		ns
Operation Recovery Time	t _B	t _{RC}		t _{RC}	l	ns



NOTE: Vcc = VDR = 3V $\overline{CSL \& CSR} \ge Vcc - 0.2$

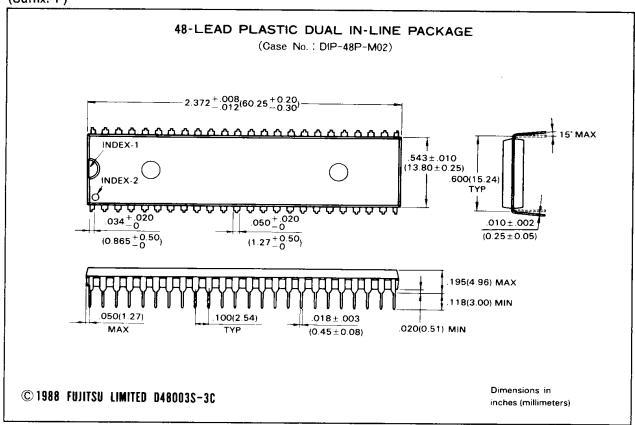
AC TEST CONDITIONS



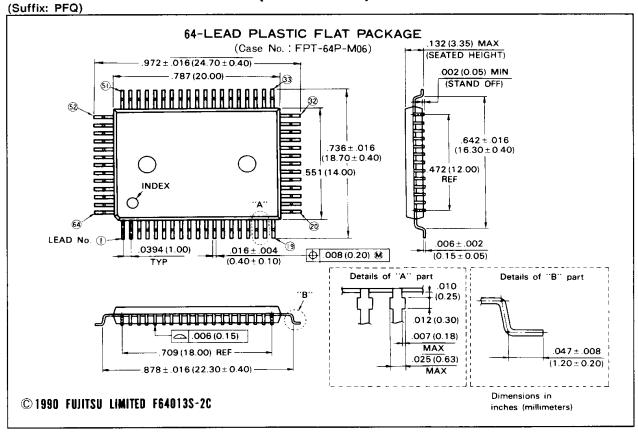
NOTE: Includes jig and stray capacitance.

PACKAGE DIMENSIONS

(Suffix: P)



PACKAGE DIMENSIONS (Continued)



PACKAGE DIMENSIONS (Continued)

